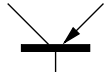
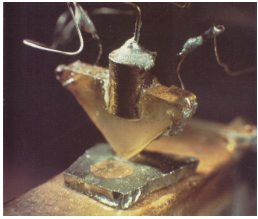
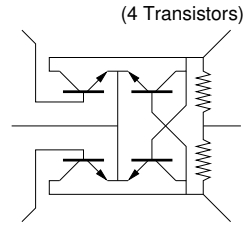
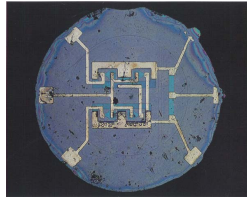


1947 Point Contact transistor

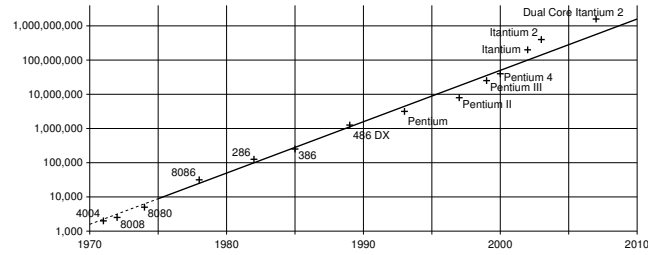


1961 Fairchild Bipolar RTL RS Flip-Flop



1965 Moore's Law (Mk I) Number of transistor has doubled every year and will continue to do so until 1975

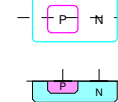
1975 Moore's Law (Mk II) Number of transistors will double every two years



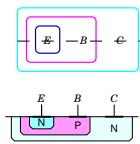
Self-fulfilling Prophecy

1000

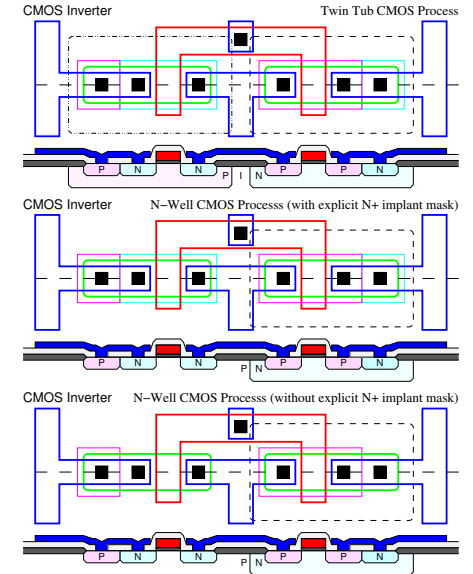
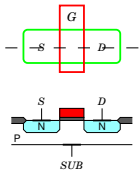
Diode



NPN Transistor



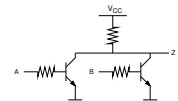
NMOS Enhancement transistor NMOS Process



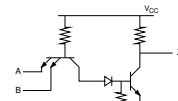
Features may be determined by a number of masks
e.g. NMOS source drain: ActiveArea AND NOT(NWell OR Poly OR PImplant)

3000

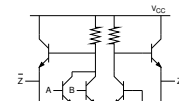
RTL NOR Gate



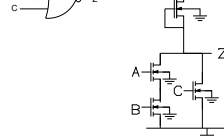
TTL NAND Gate



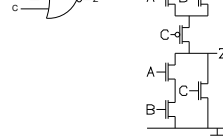
ECL OR/NOR Gate



NMOS Compound Gate



CMOS Compound Gate



• Bipolar Transistors with Resistors - MSI/LSI

RTL - NOR

TTL - NAND

ECS - OR/NOR

• MOS Transistors (no resistors) - VLSI

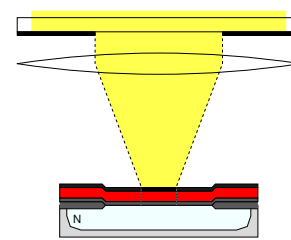
NMOS

CMOS - No static power!

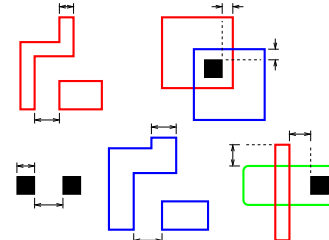
Both allow construction of NOR, NAND & Compound gate (always inverting)

2000

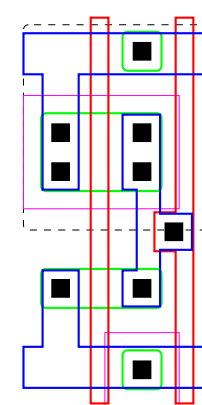
Processing



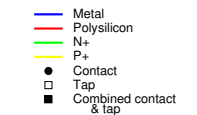
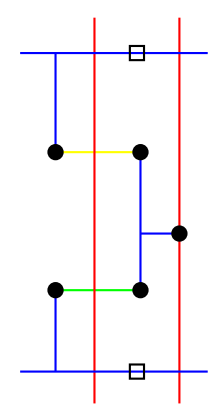
Design Rules - width, separation, overlap



Optimised Mask Layout

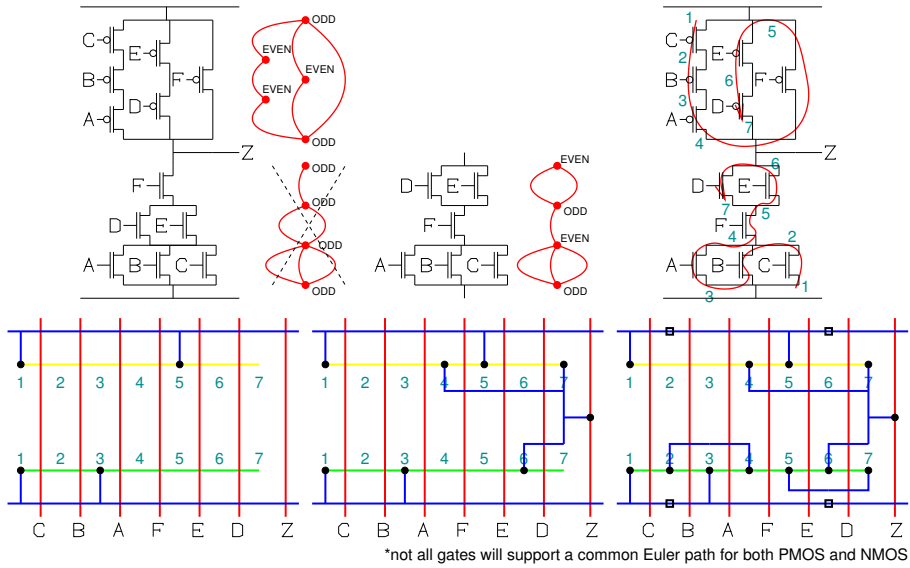


Equivalent Stick Diagram

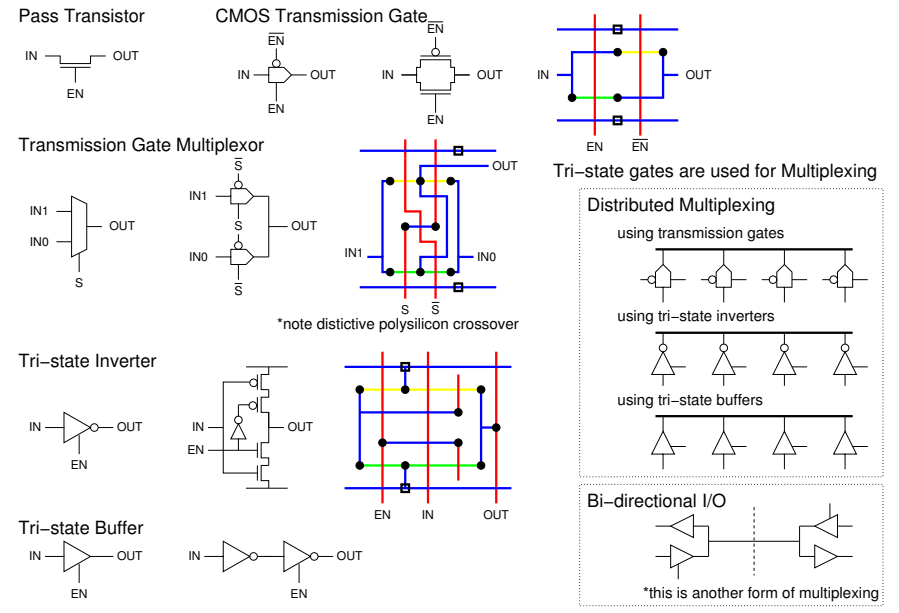


4000

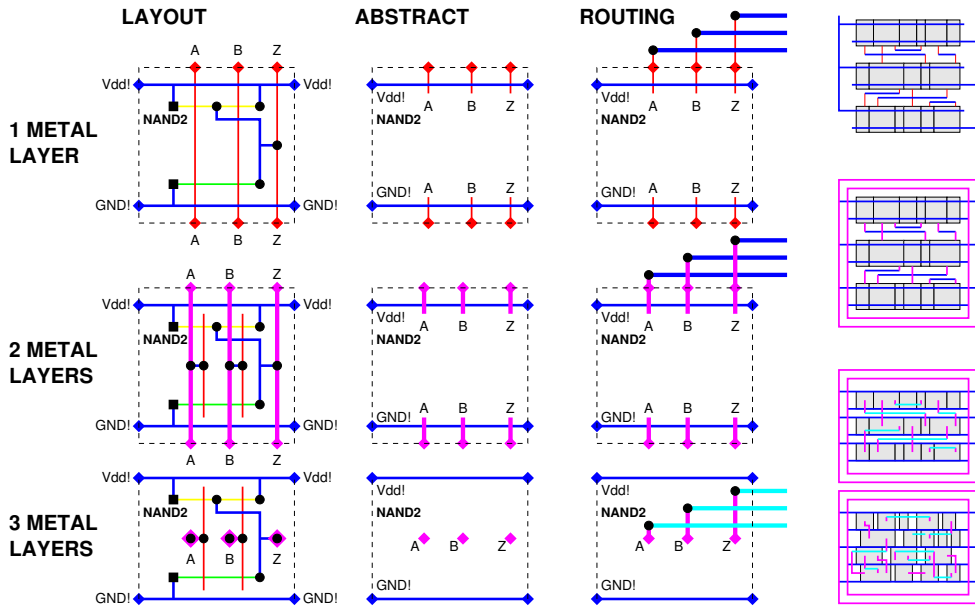
Investigation of Euler paths leads to more efficient layout*



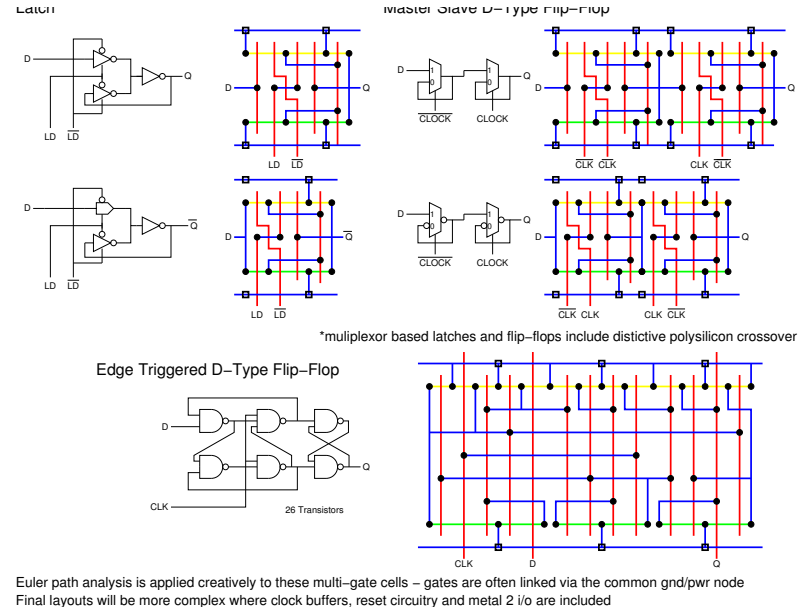
5000



7000

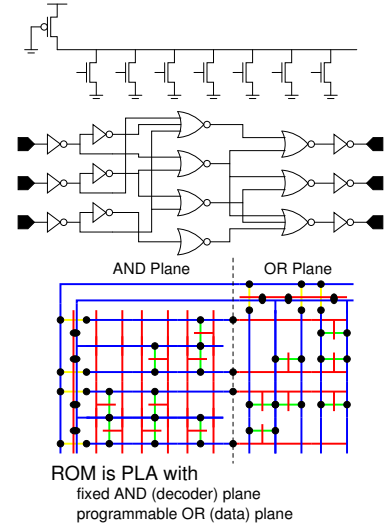


6000



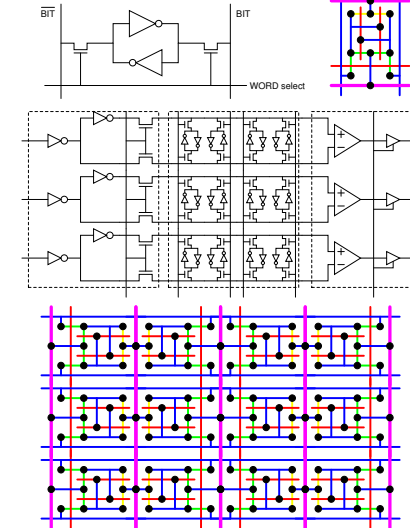
8000

PLA and ROM



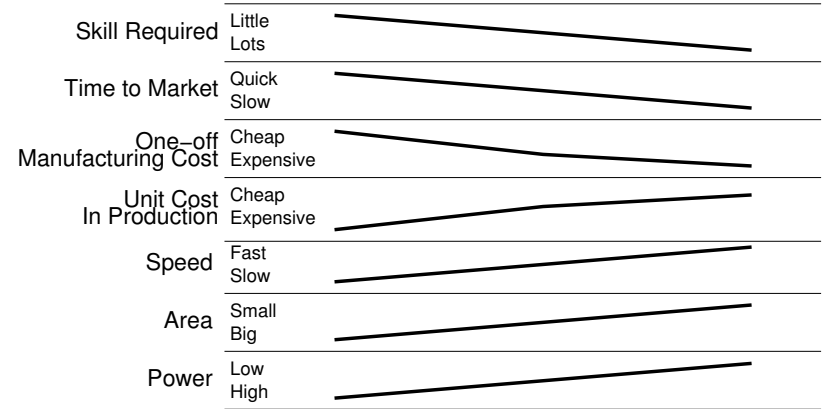
Cells are designed to butt together in two dimensions leading to efficient layout
PLA layout efficiency will depend on the actual function implemented (e.g. number of common product terms)

SRAM



9000

Programmable Logic Semi-Custom Full Custom



All design styles need full custom designers
A large ASIC (especially SoC) may mix Semi-Custom and Full Custom

10000